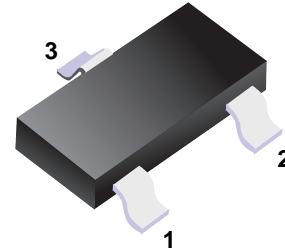


■ Simplified outline(SOT-23)

■ Features

- Collector Current:  $I_C=1.5A$



1.Base  
2.Emitter  
3.Collector

■ Absolute Maximum Ratings  $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	40	V
Collector-Emitter Voltage	$V_{CEO}$	25	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current -Continuous	$I_C$	1.5	A
Collector Dissipation	$P_C$	0.3	W
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 to 150	$^\circ C$

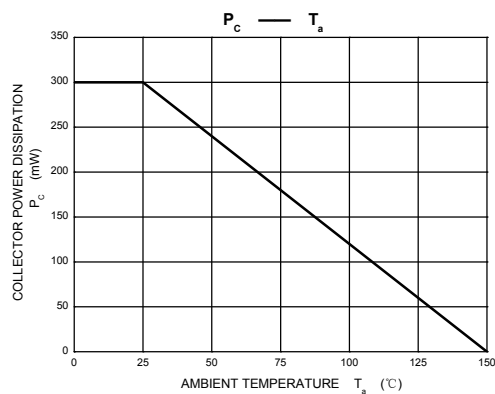
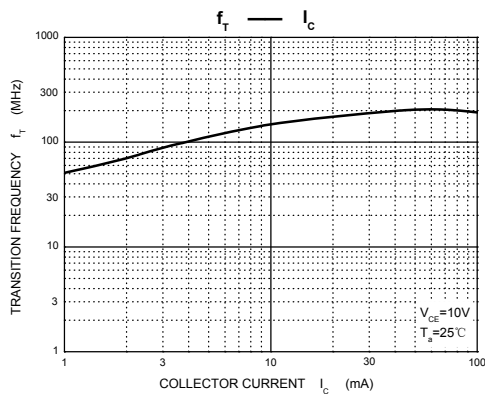
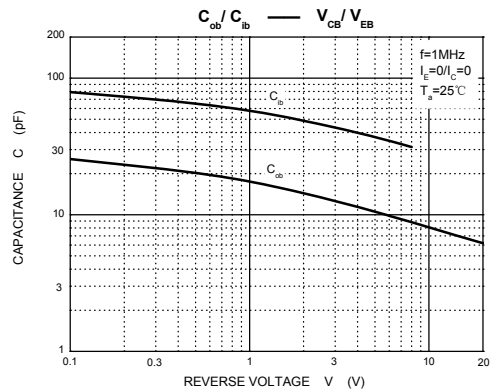
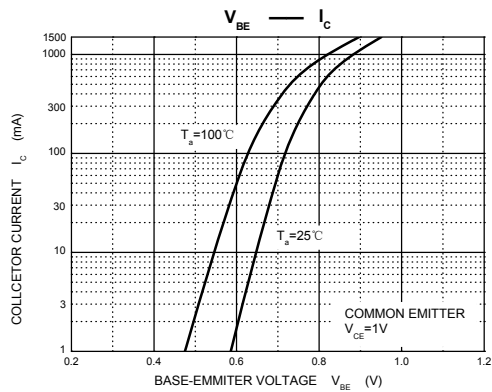
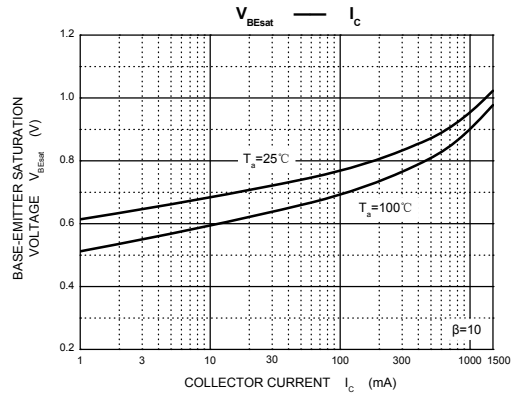
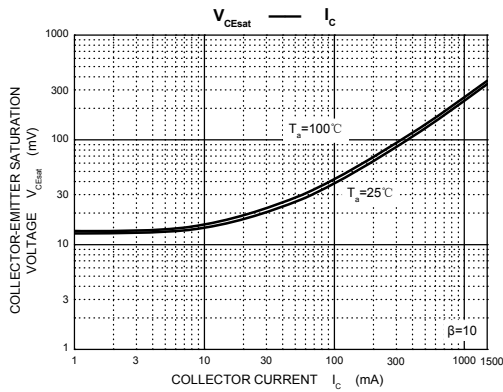
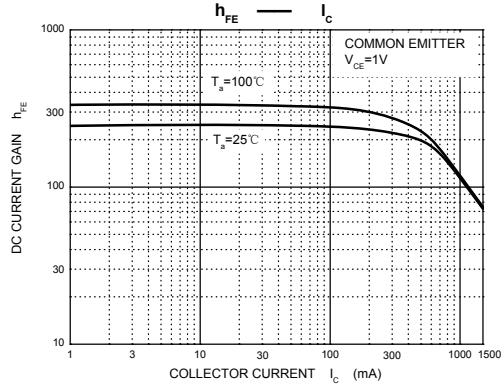
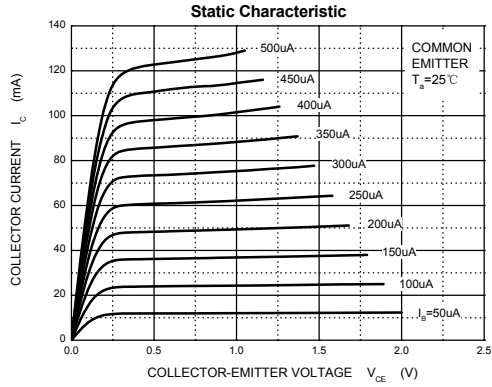
■ Electrical Characteristics  $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{CBO}$	$I_C = 100 \mu A, I_E = 0$	40			V
Collector-emitter breakdown voltage	$V_{CEO}$	$I_C = 1mA, I_B = 0$	25			V
Emitter-base Breakdown voltage	$V_{EBO}$	$I_E = 100 \mu A, I_C = 0$	5			V
Collector-base cut-off current	$I_{CBO}$	$V_{CB} = 40V, I_E = 0$			0.1	$\mu A$
Collector-emitter cut-off current	$I_{CEO}$	$V_{CE} = 20V, I_B = 0$			1	$\mu A$
Emitter-base cut-off current	$I_{EBO}$	$V_{EB} = 5V, I_C = 0$			0.1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE} = 1V, I_C = 100mA$	120		400	
		$V_{CE} = 1V, I_C = 800mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 800mA, I_B = 80mA$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 800mA, I_B = 80mA$			1.2	V
Transition frequency	$f_T$	$V_{CE} = 10V, I_C = 50mA, f = 30MHz$	100			MHz

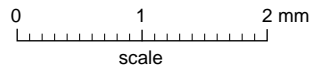
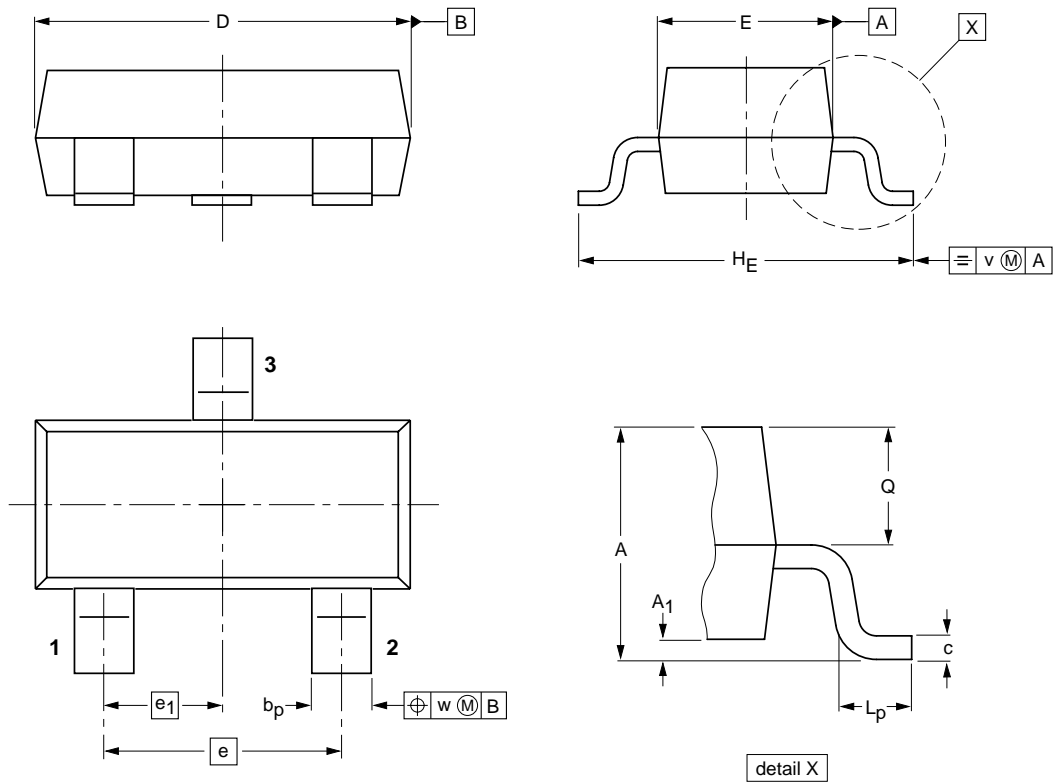
■  $h_{FE(1)}$  Classification

Type	SS8050	SS8050-L	SS8050-H	SS8050-J
Range	200-350	120-200	144-202	300-400
Marking	Y1			

■ Typical Characteristics



■ SOT-23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max.	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1